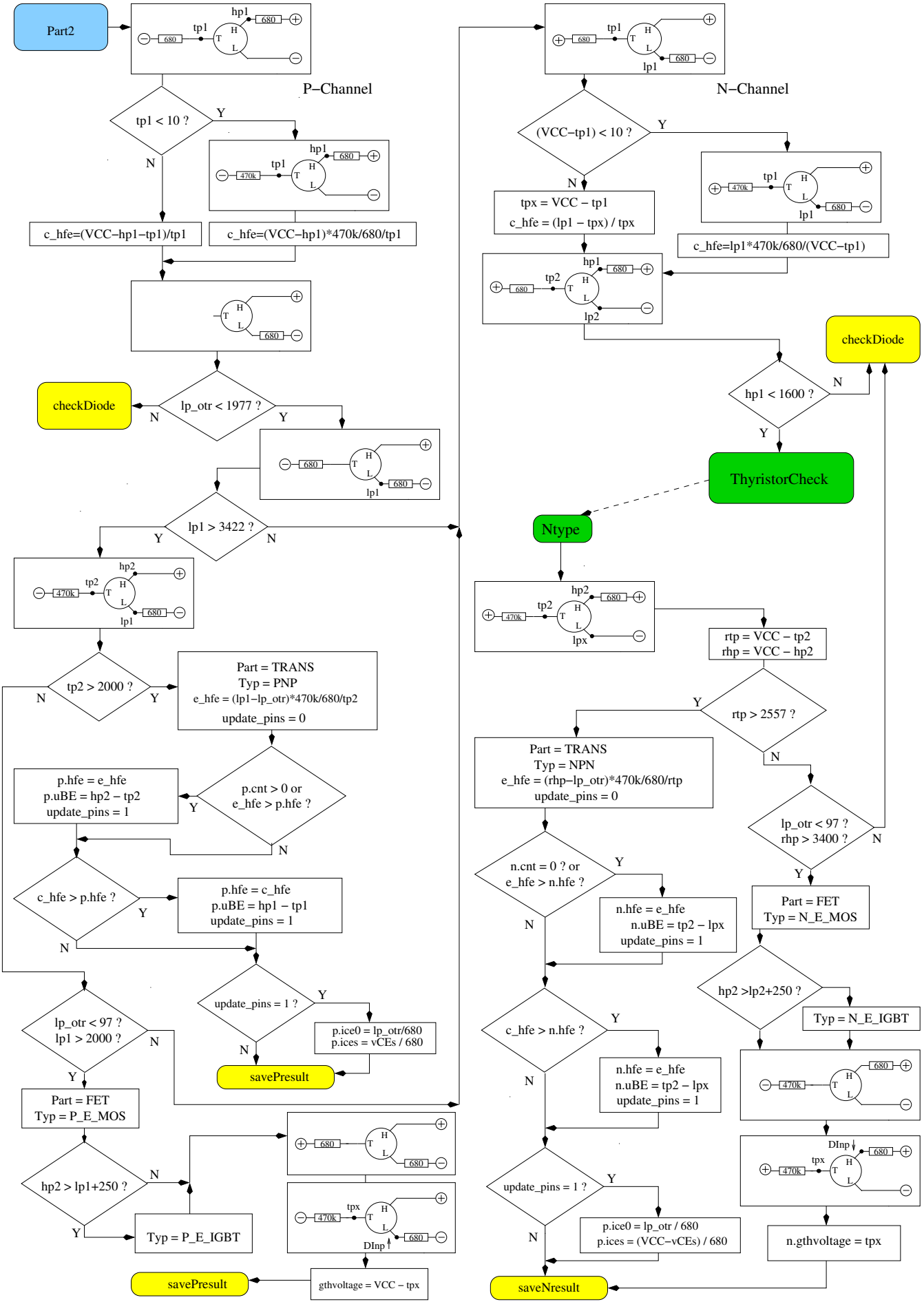
Part2
P−Channel
tp1 < 10 ?
Y
N
c_hfe=(VCC−hp1−tp1)/tp1
c_hfe=(VCC−hp1)*470k/680/tp1
checkDiode
lp_otr < 1977 ?
lp1 > 3422 ?
tp2 > 2000 ?
Part = TRANS
Typ = PNP
e_hfe = (lp1−lp_otr)*470k/680/tp2
update_pins = 0
p.cnt > 0 or
e_hfe > p.hfe ?
p.hfe = e_hfe
p.uBE = hp2 − tp2
update_pins = 1
c_hfe > p.hfe ?
p.hfe = c_hfe
p.uBE = hp1 − tp1
update_pins = 1
update_pins = 1 ?
p.ice0 = lp_otr/680
p.ices = vCEs / 680
savePresult
lp_otr < 97 ?
lp1 > 2000 ?
Part = FET
Typ = P_E_MOS
hp2 > lp1+250 ?
Typ = P_E_IGBT
gthvoltage = VCC − tpx
N−Channel
(VCC−tp1) < 10 ?
tpx = VCC − tp1
c_hfe = (lp1 − tpx) / tpx
c_hfe=lp1*470k/680/(VCC−tp1)
hp1 < 1600 ?
ThyristorCheck
Ntype
rtp = VCC − tp2
rhp = VCC − hp2
rtp > 2557 ?
Part = TRANS
Typ = NPN
e_hfe = (rhp−lp_otr)*470k/680/rtp
update_pins = 0
n.cnt = 0 ? or
e_hfe > n.hfe ?
n.hfe = e_hfe
n.uBE = tp2 − lpx
update_pins = 1
c_hfe > n.hfe ?
n.hfe = e_hfe
n.uBE = tp2 − lpx
update_pins = 1
update_pins = 1 ?
p.ice0 = lp_otr / 680
p.ices = (VCC−vCEs) / 680
saveNresult
lp_otr < 97 ?
rhp > 3400 ?
Part = FET
Typ = N_E_MOS
hp2 >lp2+250 ?
Typ = N_E_IGBT
n.gthvoltage = tpx